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CLAIMS

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What is claimed is:

1. A\capacitor structure, comprising:

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a bottom plate and a top plate, said top plate having a perimeter;

a dielectric layer in between said bottom plate and said top plate; and

at least one insulating sidewall spacer placed against said perimeter of said top plate and overlaying a portion of said dielectric layer.

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2. The capacitor structure of Claim 1, and further comprising:

a substrate underlying said bottom plate; and

- a conductor embedded in said substrate and underlying said bottom plate.
- 3. The capacitor structure of Claim 2, wherein said conductor comprises copper damascene.
- 4. The capacitor structure of Claim 3, said bottom plate further comprising a conductive barrier layer in contact with said conductor.
- 5. The capacitor structure of Claim 1, wherein each of said bottom plate and said top plate comprises a metal plate.
- 6. The capacitor structure of Claim 1, wherein said dielectric layer comprises silicon dioxide.
- 7. The capacitor structure of Claim 1, and further comprising an insulating cap overlaying said top plate.

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8. The capacitor structure of Claim 7, wherein said insulating cap has a corresponding perimeter to said top plate, and wherein said at least one insulating sidewall spacer is placed against said perimeter of said insulating cap.

9. A method of fabricating a capacitor structure, said method comprising:

forming a bottom plate;

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forming a dielectric layer overlaying the bottom

plate;

forming a top plate over the dielectric layer, said top plate having a perimeter;

forming at least one insulating sidewall spacer placed against said perimeter of said top plate and overlaying a portion of said dielectric layer.

10. The method of Claim 9, and further comprising:

prior to forming said at least one insulating sidewall spacer, etching said top plate to expose said dielectric at said perimeter of said top plate.

11. The method of Claim\9, wherein:

said method further comprises forming a conductor embedded in a substrate; and

forming the bottom plate comprises forming the bottom plate overlaying the conductor.

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- 12. The method of Claim 11, wherein forming a conductor comprises forming a copper damascene structure.
- 13. The method of Claim 11, wherein forming said bottom plate comprises forming a conductive barrier layer in contact with said conductor.
- 14. The method of Claim 9, wherein each of said steps of forming a bottom plate and forming a top plate comprises forming a metal plate.
- 15. The method of Claim 9, wherein forming the dielectric layer comprises forming a silicon dioxide layer.
- 16. The method of Claim 9, and further comprising forming an insulating cap overlaying said top plate.
- 17. The method of Claim 16, wherein said insulating cap has a corresponding perimeter to said top plate, and wherein forming said at least one insulating sidewall spacer comprising forming said at least one insulating sidewall spacer against said perimeter of said insulating cap.

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